TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP124

Office Machine Programmable Controllers AC / DC–Input Module Telecommunication

The TOSHIBA mini flat coupler TLP124 is a small outline coupler, suitable for surface mount assembly. TLP124 consists of a photo transistor optically coupled to a gallium arsenide infrared emitting diode.

- Collector-emitter voltage: 80 V min.
- Current transfer ratio: 100% min. Rank BV: 200% min.
- Isolation voltage: 3750Vrms min.
- UL recognized: UL1577, file No. E67349



Pin Configurations (top view)



1 : Anode

- 3 : Cathode 4 : Emitter
- 6 : Collector

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Current Transfer Ratio

Classification	Curr			
	Ta = 25°C		Ta = –25~75°C	Marking Of
Classification	I _F = 1mA V _{CE} = 0.5V	I _F = 0.5mA V _{CE} = 1.5V	I _F = 1mA V _{CE} = 0.5V	Classification
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV, Blank

(Note) Application type name for certification test, please use standard product type name, i. e. TLP124 (BV): TLP124

Maximum Rations (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	١ _F	50	mA
	Forward current derating	ΔI _F / °C	–0.7 (Ta ≥ 53°C)	mA / °C
LED	Peak forward current (100µs pulse, 100pps)	I _{FP}	1	А
	Reverse voltage	V _R	5	V
	Junction temperature	Тj	125	°C
	Collector-emitter voltage	V _{CEO}	80	V
	Emitter-collector valtage	V _{ECO}	7	V
	Collector current	Ι _C	50	mA
Detector	ອຼັ Peak collector current (10ms pulse, 100pps)	I _{CP}	100	mA
De	Power dissipation	P _C	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _C /°C	-1.5	mA / °C
	Junction temperature	Тj	125	°C
Stor	age temperature range	T _{stg}	-55~125	°C
Оре	erating temperature range	T _{opr}	-55~100	°C
Lea	d soldering temperature (10s)	T _{sol}	260	°C
Tota	al package power dissipation	PT	200	mW
	al package power dissipation ating (Ta $\ge 25^{\circ}$ C)	ΔP _T / °C	-2.0	mW / °C
	ation voltage , 1min., R.H. ≤ 60%) (Note 1)	BVS	3750	Vrms

(Note 1) Device considered a two terminal device: Pins1, 3 shorted together and pins 4, 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	48	V
Forward current	١ _F		1.6	20	mA
Collector current	Ι _C		1	10	mA
Operating temperature	T _{opr}	-25		75	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	80			V
Detector	Emitter–collector breakdown voltage	V _{(BR) ECO}	I _E = 0.1 mA	7			V
Dete	Collector dark current	la la	V _{CE} = 48 V	_	10	100	nA
		Ι _D	V _{CE} = 48 V, Ta = 85°C		2	50	μA
	Capacitance collector to emitter	C _{CE}	V = 0, f = 1 MHz		12	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Mln.	Тур.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 1mA, V _{CE} = 0.5 V	100	_	1200	%
	IC / IF	IF Rank BV	200	_	1200	
Low input CTR	I _C / I _{F (low)}	I _F = 0.5 mA, V _{CE} = 1.5 V Rank BV	50			%
			100	-		
	V _{CE (sat)}	I _C = 0.5 mA, I _F = 1 mA	_	_	0.4	
Collector-emitter saturation voltage		I _C = 1 mA, I _F = 1 mA Rank BV	_	0.2	_	V
			_	_	0.4	
Off-state collector current	I _{C(off)}	V _F = 0.7V, V _{CE} = 48 V	-	-	10	μA

Coupled Electrical Characteristics (Ta = -25~75°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	IC / IF	I _F = 1mA, V _{CE} = 0.5 V Rank BV	50	_	_	%
	IC / IF		100	_	_	%
Low input CTR		I _F = 0.5 mA, V _{CE} = 1.5 V		50		%
	I _C / I _{F (low)}	Rank BV	_	100	_	%

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴		Ω
		AC, 1 minute	3750	_		V
Isolation voltage	BVS	AC, 1 s, in oil	_	10000	_	V _{rms}
		DC, 1 minute, in oil	—	10000	-	V _{dc}

Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t _r		_	8	_	
Fall time	t _f	V_{CC} = 10 V, I _C = 2 mA R _L = 100Ω	_	8	—	μs
Turn–on time	t _{ON}	R _L = 100Ω	_	10	—	μο
Turn-off time	tOFF		_	8	—	
Turn–on time	t _{ON}		_	10	—	
Storage time	ts	$R_L = 4.7 k\Omega$ (Fig.1) V _{CC} = 5 V, I _F = 1.6 mA	_	50	_	μs
Turn–off time	t _{OFF}		_	300	_	

Fig. 1 Switching time test circuit





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Switching Time – RL Ta = 25°C IF = 1.6mA VCC = 5V tOFF Switching time (µs) tON 1 Load resistance R_L (k Ω)

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